WESTCODE

An IXYS Company

Date:- 22 June, 2011

Data Sheet Issue:- P1

Prospectve Data

Medium Voltage Thyristor

Type K1000M#600 to K1000M#650

Development Type No. KX283M#600-650

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{DRM}	Repetitive peak off-state voltage, (note 1)	6000-6500	V
V_{DSM}	Non-repetitive peak off-state voltage, (note 1)	6000-6500	V
V_{RRM}	Repetitive peak reverse voltage, (note 1)	6000-6500	V
V_{RSM}	Non-repetitive peak reverse voltage, (note 1)	6100-6600	V

	OTHER RATINGS		MAXIMUM LIMITS	UNITS
$I_{T(AV)M}$	Maximum average on-state current, T_{sink}=55°C, (note 2)		1000	A
$I_{T(AV)M}$	Maximum average on-state current. T_{sink}=85°C, (note 2)		695	A
$I_{T(AV)M}$	Maximum average on-state current. T_{sink}=85°C, (note 3)		410	A
$I_{T(RMS)}$	Nominal RMS on-state current, T_{sink}=25°C, (note 2)		1950	A
$I_{T(d.c.)}$	D.C. on-state current, T_{sink}=25°C, (note 4)		1735	A
I_{TSM}	Peak non-repetitive surge t_p=10ms, V_{rm}=60%V_{RRM}, (note 5)		12.5	kA
I_{TSM2}	Peak non-repetitive surge t_p=10ms, V_{rm}≤10V, (note 5)		13.7	kA
I^2t	I^2t capacity for fusing t_p=10ms, V_{rm}=60%V_{RRM}, (note 5)		781×10^3	A^2s
I^2t	I^2t capacity for fusing t_p=10ms, V_{rm}≤10V, (note 5)		938×10^3	A^2s
$(di/dt)_{cr}$	Critical rate of rise of on-state current, (Note 6)	continuous, 50Hz	100	A/µs
		repetitive, 50Hz, 60s	200	
		non-repetitive	700	
V_{RGM}	Peak reverse gate voltage		5	V
$P_{G(AV)}$	Mean forward gate power		2	W
P_{GM}	Peak forward gate power		30	W
$T_{j\ op}$	Operating temperature range		-40 to +125	°C
T_{stg}	Storage temperature range		-40 to +150	°C

Notes:-

1) De-rating factor of 0.13% per °C is applicable for T_j below 25°C.
2) Double side cooled, single phase; 50Hz, 180° half-sinewave.
3) Cathode side cooled, single phase; 50Hz, 180° half-sinewave.
4) Double side cooled.
5) Half-sinewave, 125°C T_j initial.
6) V_D=67% V_{DRM}, I_{FG}=2A, t_r≤0.5µs, T_{case}=125°C.

Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V_{TM}	Maximum peak on-state voltage	2.05	-	2.25	I_{TM}=1000A	V
V_{TM}	Maximum peak on-state voltage	-	-	3.97	I_{TM}=3000A	V
V_{T0}	Threshold voltage	-	-	1.39		V
r_T	Slope resistance	-	-	0.86		mΩ
$(dv/dt)_{cr}$	Critical rate of rise of off-state voltage	1000	-	-	V_D=80% V_{DRM}, linear ramp, gate o/c	V/µs
I_{DRM}	Peak off-state current	-	-	100	Rated V_{DRM}	mA
I_{RRM}	Peak reverse current	-	-	100	Rated V_{RRM}	mA
V_{GT}	Gate trigger voltage	-	-	1.80	T_j=25°C. V_D=10V, I_T=3A	V
I_{GT}	Gate trigger current	-	-	300		mA
V_{GD}	Gate non-trigger voltage	-	-	0.25	Rated V_{DRM}	V
I_H	Holding current	-	-	1000	T_j=25°C	mA
t_{gd}	Gate-controlled turn-on delay time	-	0.5	1.5	V_D=67% V_{DRM}, I_T=2000A, di/dt=10A/µs, I_{FG}=2A, t_r=0.5µs, T_j=25°C	µs
t_{gt}	Turn-on time	-	2.0	5.0		µs
Q_{rr}	Recovered charge	6000	-	7000	I_{TM}=2000A, t_p=1000µs, di/dt=10A/µs, V_r=100V	µC
Q_{ra}	Recovered charge, 50% chord	-	3250	-		µC
I_{rm}	Reverse recovery current	160	-	180		A
t_{rr}	Reverse recovery time, 50% chord	-	40	-		µs
t_q	Turn-off time	700	-	-	I_{TM}=2000A, t_p=1000µs, di/dt=10A/µs, V_r=100V, V_{dr}=27%V_{DRM}, dV_{dr}/dt=20V/µs	µs
		1000	-	-	I_{TM}=2000A, t_p=1000µs, di/dt=10A/µs, V_r=100V, V_{dr}=67%V_{DRM}, dV_{dr}/dt=200V/µs	
R_{thJK}	Thermal resistance, junction to heatsink	-	-	0.020	Double side cooled	K/W
		-	-	0.038	Anode side cooled	K/W
		-	-	0.043	Cathode side cooled	K/W
F	Mounting force	25	-	31		kN
W_t	Weight	-	550	-	Housing option MA	g
		-	730	-	Housing option ME	g

Notes:-

1) Unless otherwise indicated T_j=125°C.
2) For other clamp forces consult factory.

Curves

Figure 1 – On-state characteristics of Limit device

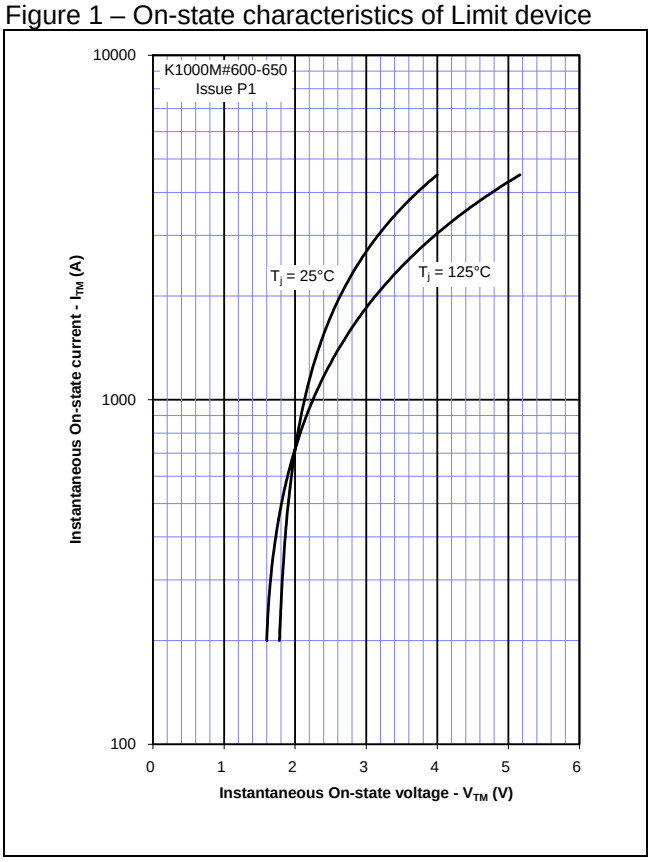


Figure 2 – Transient thermal impedance

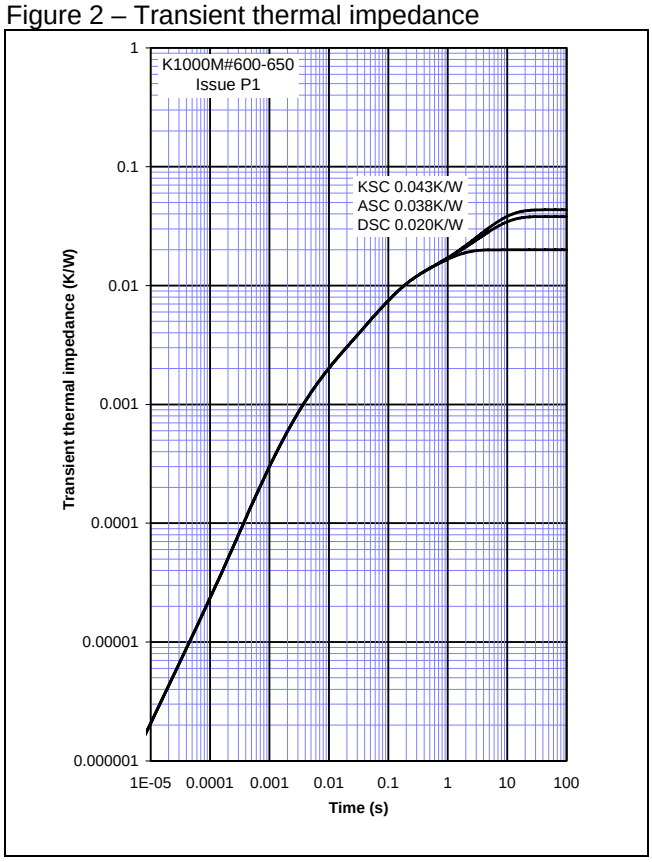
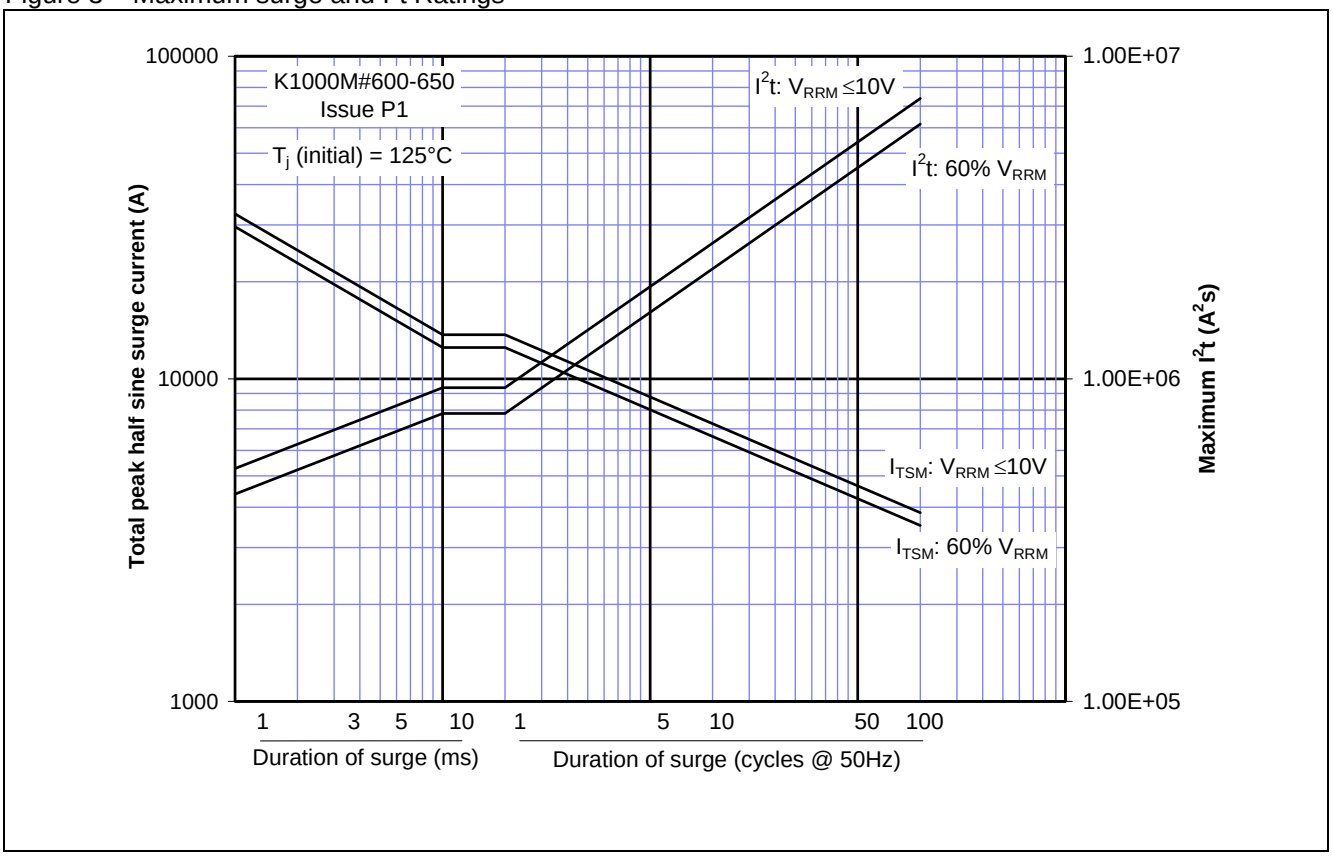
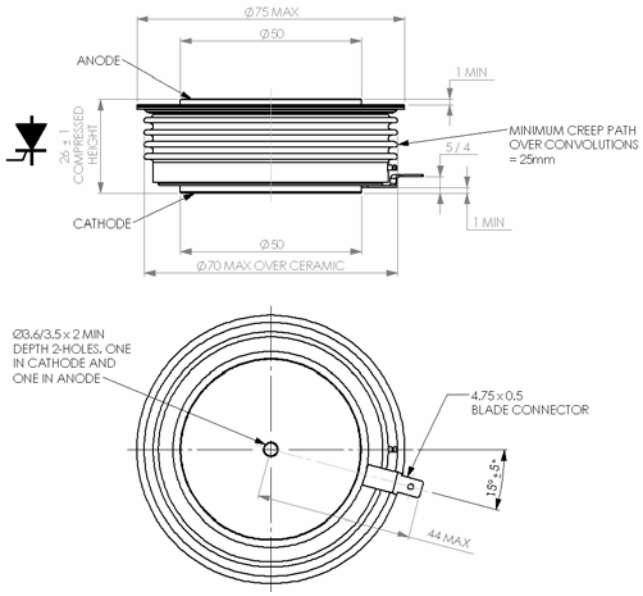


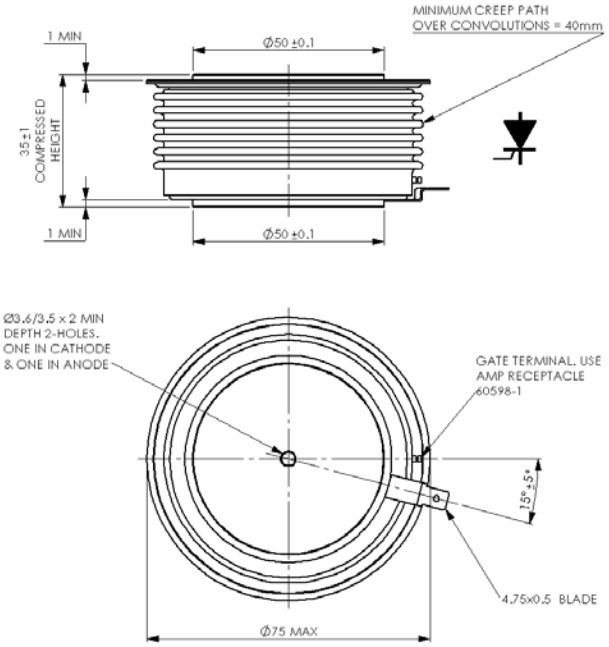
Figure 3 – Maximum surge and I^2t Ratings



Outline Drawing & Ordering Information



Outline option MA



Outline option ME

ORDERING INFORMATION		(Please quote 10 digit code as below)	
K1000	**Q#**	**♦♦**	**0**
Fixed Type Code	Outline Code MA=26mm ME=35mm	Voltage code V_{RRM}/100 60-65	Fixed code

Typical order code: K1000MA650 – 6500V V_{DRM}, V_{RRM}, 26mm clamp height capsule.

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